

01 July 2003

Updated Search

09/834,308

L Number	Hits	S arch Text	DB	Time stamp
1	4	216/58,83.ccls. and (diffraction adj (grate or grating))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 10:34
2	163	216/\$.ccls. and (diffraction adj (grate or grating))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 10:40
3	6	(216/\$.ccls. and (diffraction adj (grate or grating))) and (solar or photovoltaic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 10:38
4	42	(216/\$.ccls. and (diffraction adj (grate or grating))) and (reactive adj ion adj etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 10:41
5	26	216/\$.ccls. and ((diffraction adj (grate or grating)) with (transmi\$7 or transparent))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 10:41
6	7	(216/\$.ccls. and ((diffraction adj (grate or grating)) with (transmi\$7 or transparent))) and (reactive adj ion adj etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 11:25
7	343	136/\$.ccls. and (ion adj implantation)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 11:25
8	41	(136/\$.ccls. and (ion adj implantation)) and (diffraction or diffractive)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 11:25
9	3	(136/\$.ccls. and (ion adj implantation)) and ((diffraction or diffractive) adj grating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:03
10	27	136/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean or remov\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:08
11	0	216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:08
13	27	136/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or remov\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:08
12	93	216/\$.ccls. and ((ri or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:18

14	76	(216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:15
15	17	(216/\$.ccls. and ((rie or (reactiv adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) not silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:16
16	76	(216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) not ((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) not silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:16
17	0	((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) not ((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3))) not silicon)) and ((clean\$5 or contamin\$7) with ((potassium adj hydroxide) or koh! or (wet adj chemical adj etch\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19
18	180	216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19
19	33	(216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19
20	147	(216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not ((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19
21	0	((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not ((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not silicon)) and ((clean\$5 or contamin\$7) with ((potassium adj hydroxide) or koh! or (wet adj chemical adj etch\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19
22	2	((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not ((216/\$.ccls. and ((rie or (reactive adj ion adj etch\$3)) with (contamin\$7 or clean\$3 or damag\$3))) not silicon)) and ((clean\$5 or contamin\$7 or damag\$4) with ((potassium adj hydroxide) or koh! or (wet adj chemical adj etch\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 12:19